

NTMFS4835N

MOSFET – Power, Single, N-Channel, SO-8FL 30 V, 104 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These are Pb-Free Devices

Applications

- Refer to Application Note AND8195/D
- CPU Power Delivery
- DC-DC Converters
- Low Side Switching

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	30	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	I_D	$T_A = 25^\circ\text{C}$	20
		$T_A = 85^\circ\text{C}$	14
Power Dissipation $R_{\theta JA}$ (Note 1)	P_D	$T_A = 25^\circ\text{C}$	2.27
		$T_A = 85^\circ\text{C}$	0.89
Continuous Drain Current $R_{\theta JA}$ (Note 2)	I_D	$T_A = 25^\circ\text{C}$	12
		$T_A = 85^\circ\text{C}$	9.0
Power Dissipation $R_{\theta JA}$ (Note 2)	P_D	$T_A = 25^\circ\text{C}$	0.89
		$T_A = 85^\circ\text{C}$	0.89
Continuous Drain Current $R_{\theta JC}$ (Note 1)	I_D	$T_C = 25^\circ\text{C}$	104
		$T_C = 85^\circ\text{C}$	75
Power Dissipation $R_{\theta JC}$ (Note 1)	P_D	$T_C = 25^\circ\text{C}$	62.5
		$T_C = 85^\circ\text{C}$	62.5
Pulsed Drain Current	I_{DM}	208	A
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)	I_S	52	A
Drain to Source DV/DT	d_V/d_t	6	V/ns
Single Pulse Drain-to-Source Avalanche Energy $T_J = 25^\circ\text{C}, V_{DD} = 50\text{ V}, V_{GS} = 10\text{ V}, I_L = 28\text{ A}_{pk}, L = 1.0\text{ mH}, R_G = 25\ \Omega$	E_{AS}	392	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

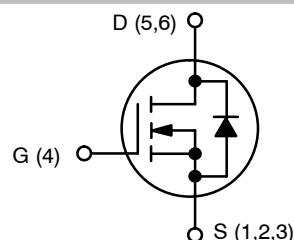
1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.



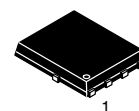
ON Semiconductor®

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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
30 V	3.5 m Ω @ 10 V	104 A
	5.0 m Ω @ 4.5 V	

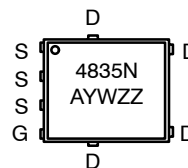


N-CHANNEL MOSFET



SO-8 FLAT LEAD
CASE 488AA
STYLE 1

MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4835NT1G	SO-8FL (Pb-Free)	1500 / Tape & Reel
NTMFS4835NT3G	SO-8FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	2.0	°C/W
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	55.1	
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	140.1	

3. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			22.4		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.5	1.9	2.5	V	
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			5.3		mV/°C	
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V to } 11.5\text{ V}$	$I_D = 30\text{ A}$		2.9	3.5	m Ω
			$I_D = 15\text{ A}$		2.5		
		$V_{GS} = 4.5\text{ V}$	$I_D = 30\text{ A}$		4.3	5.0	
			$I_D = 15\text{ A}$		3.9		
Forward Transconductance	g_{FS}	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		21		S	

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 12\text{ V}$	1860	3100	4340	pF
Output Capacitance	C_{OSS}		402	670	938	
Reverse Transfer Capacitance	C_{RSS}		216	360	504	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		22	39	nC
Threshold Gate Charge	$Q_{G(TH)}$			4.7		
Gate-to-Source Charge	Q_{GS}			8.3		
Gate-to-Drain Charge	Q_{GD}			8.8		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		52		nC

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$		16		ns
Rise Time	t_r			31		
Turn-Off Delay Time	$t_{d(OFF)}$			22		
Fall Time	t_f			13		
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$		10		ns
Rise Time	t_r			23		
Turn-Off Delay Time	$t_{d(OFF)}$			30		
Fall Time	t_f			10		

5. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 30\text{ A}$	$T_J = 25^\circ\text{C}$		0.77	1.0	V
			$T_J = 125^\circ\text{C}$		0.70		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 30\text{ A}$			27	50	ns
Charge Time	t_a				15		
Discharge Time	t_b				12		
Reverse Recovery Charge	Q_{RR}				18		

PACKAGE PARASITIC VALUES

Source Inductance	L_S	$T_A = 25^\circ\text{C}$		0.65		nH
Drain Inductance	L_D			0.005		nH
Gate Inductance	L_G			1.84		nH
Gate Resistance	R_G			1.3	5.0	Ω

5. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
6. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

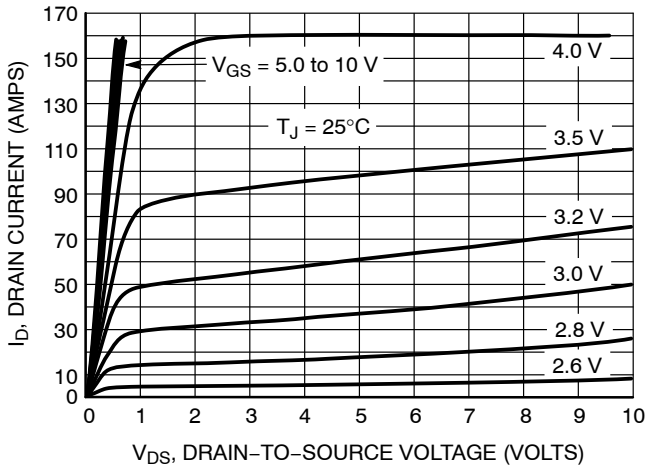


Figure 1. On-Region Characteristics

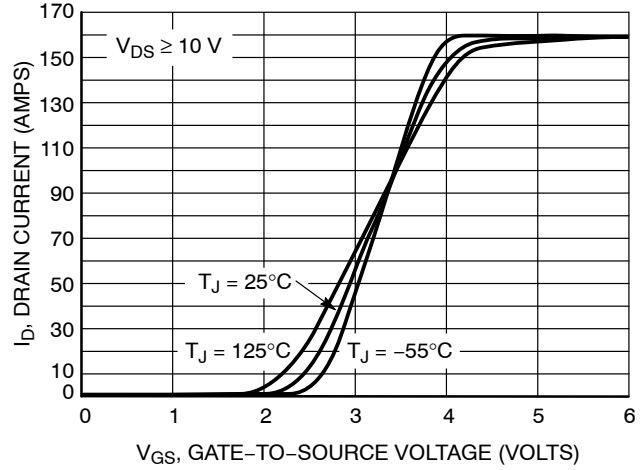


Figure 2. Transfer Characteristics

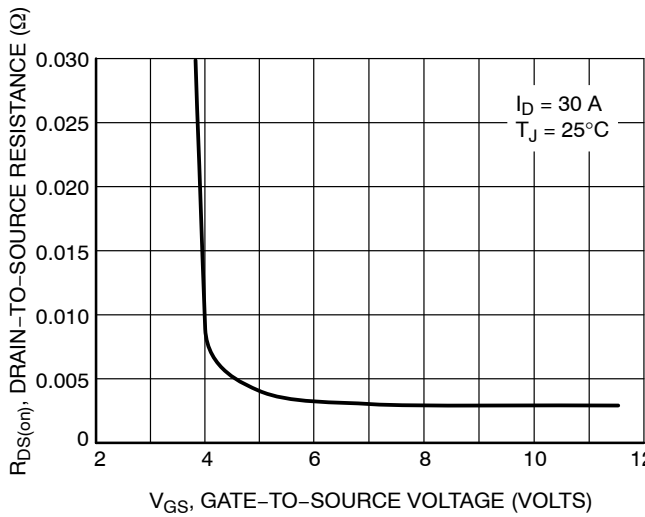


Figure 3. On-Resistance vs. Gate-to-Source Voltage

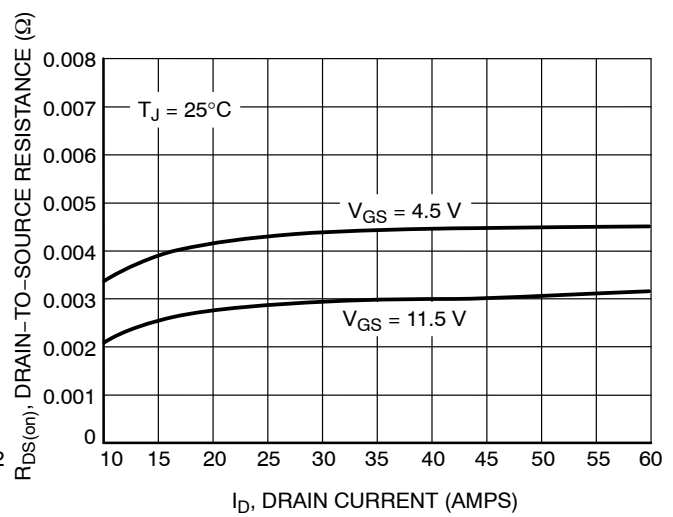


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

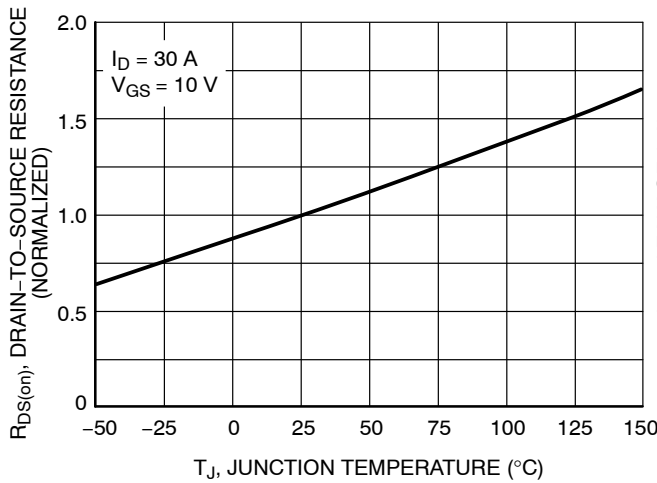


Figure 5. On-Resistance Variation with Temperature

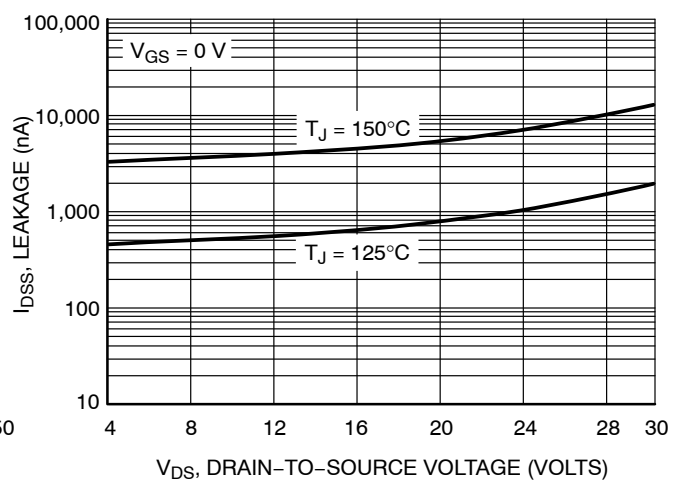


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

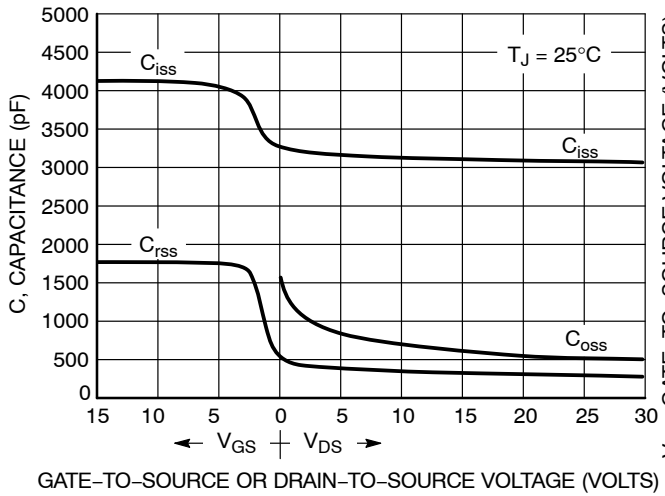


Figure 7. Capacitance Variation

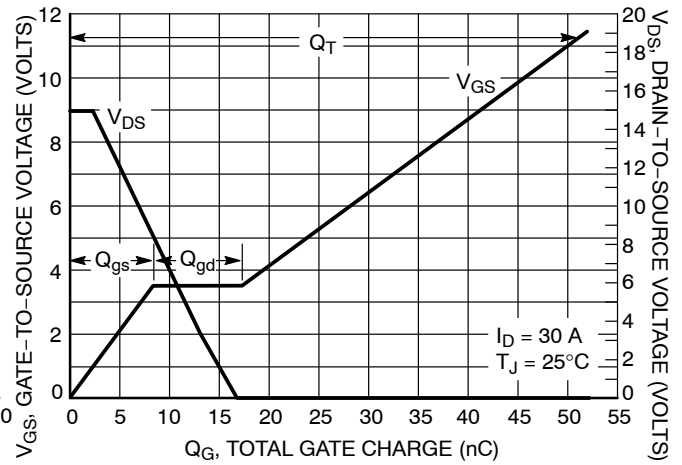


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

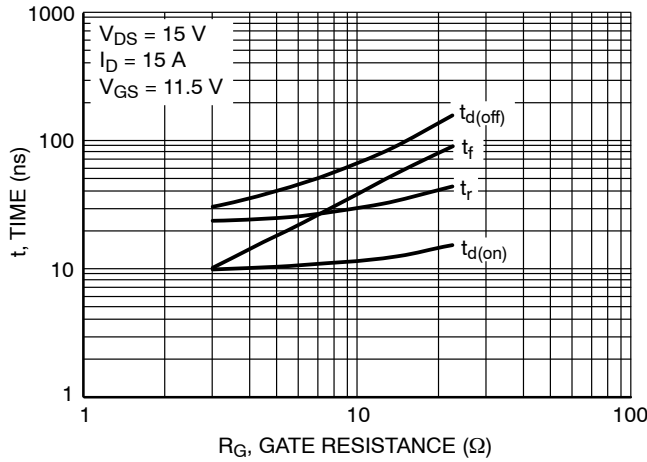


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

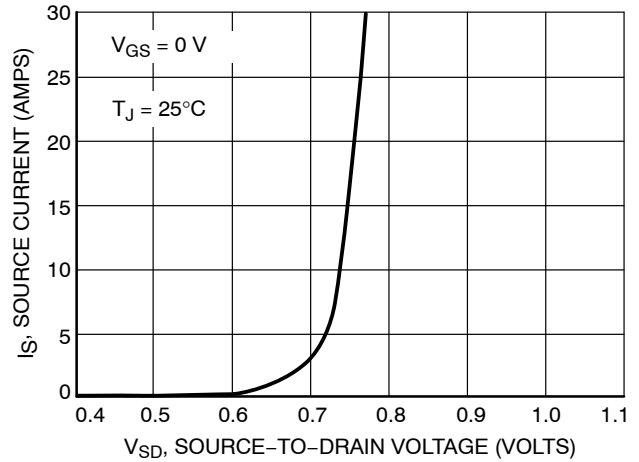


Figure 10. Diode Forward Voltage vs. Current

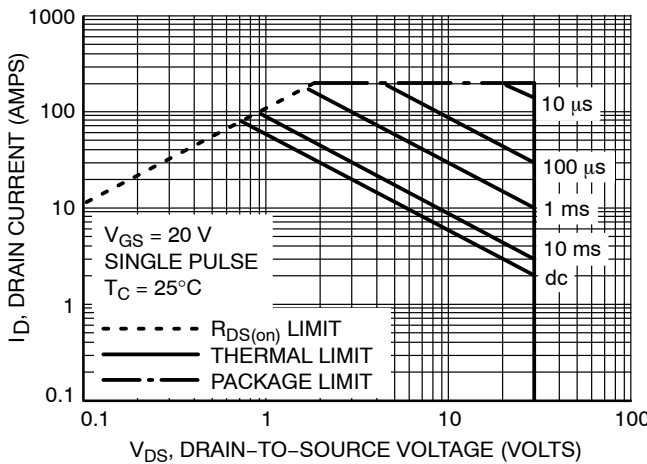


Figure 11. Maximum Rated Forward Biased Safe Operating Area

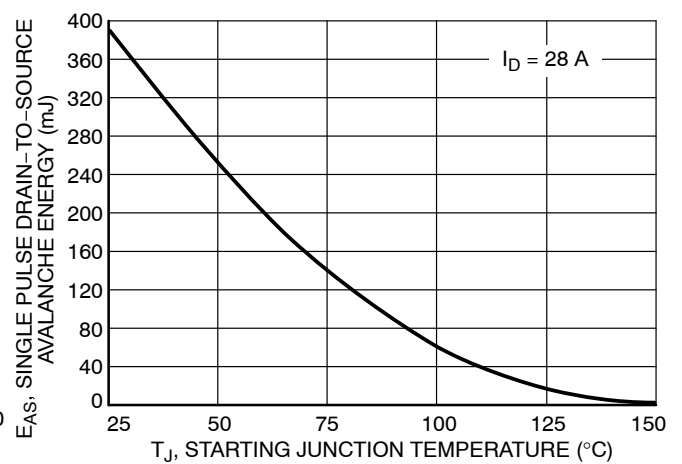


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL PERFORMANCE CURVES

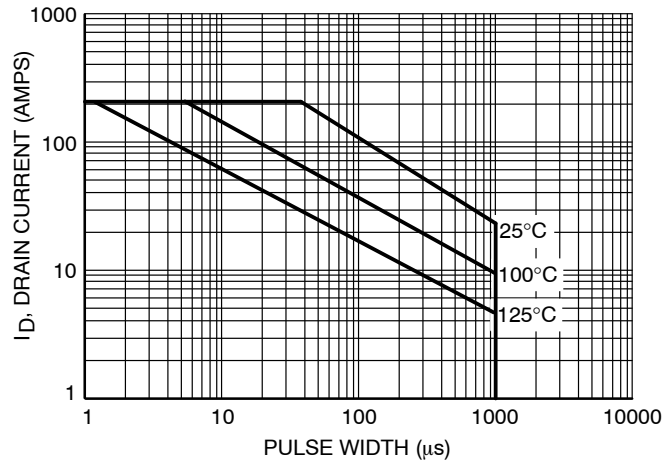


Figure 13. Avalanche Characteristics

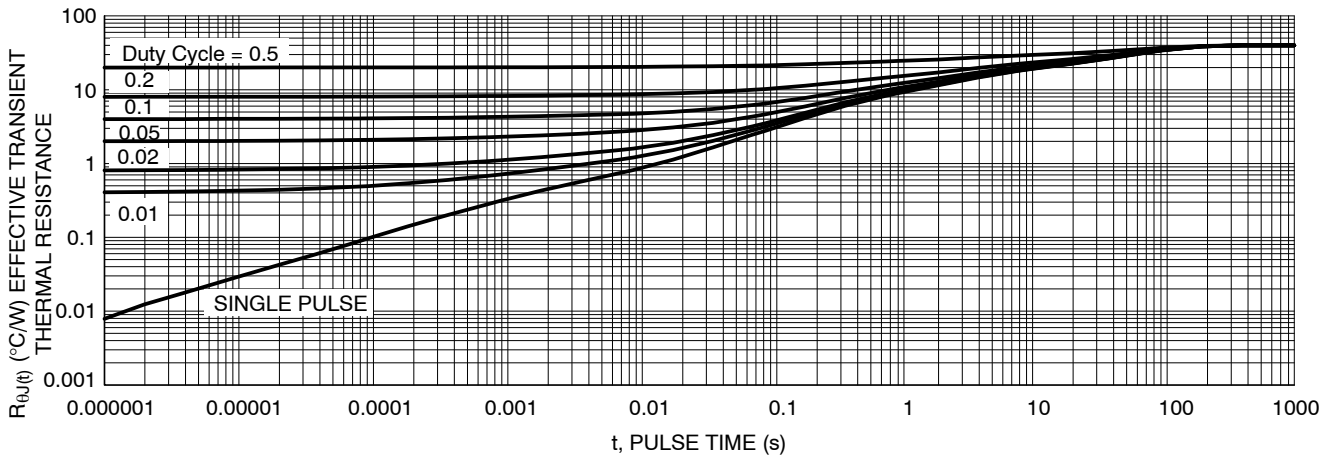


Figure 14. FET Thermal Response

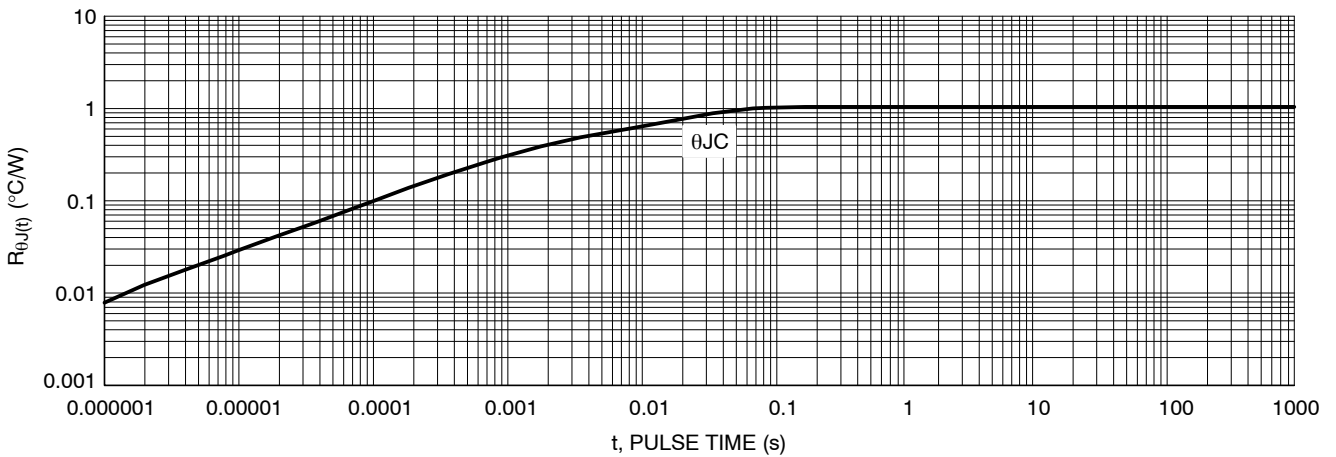
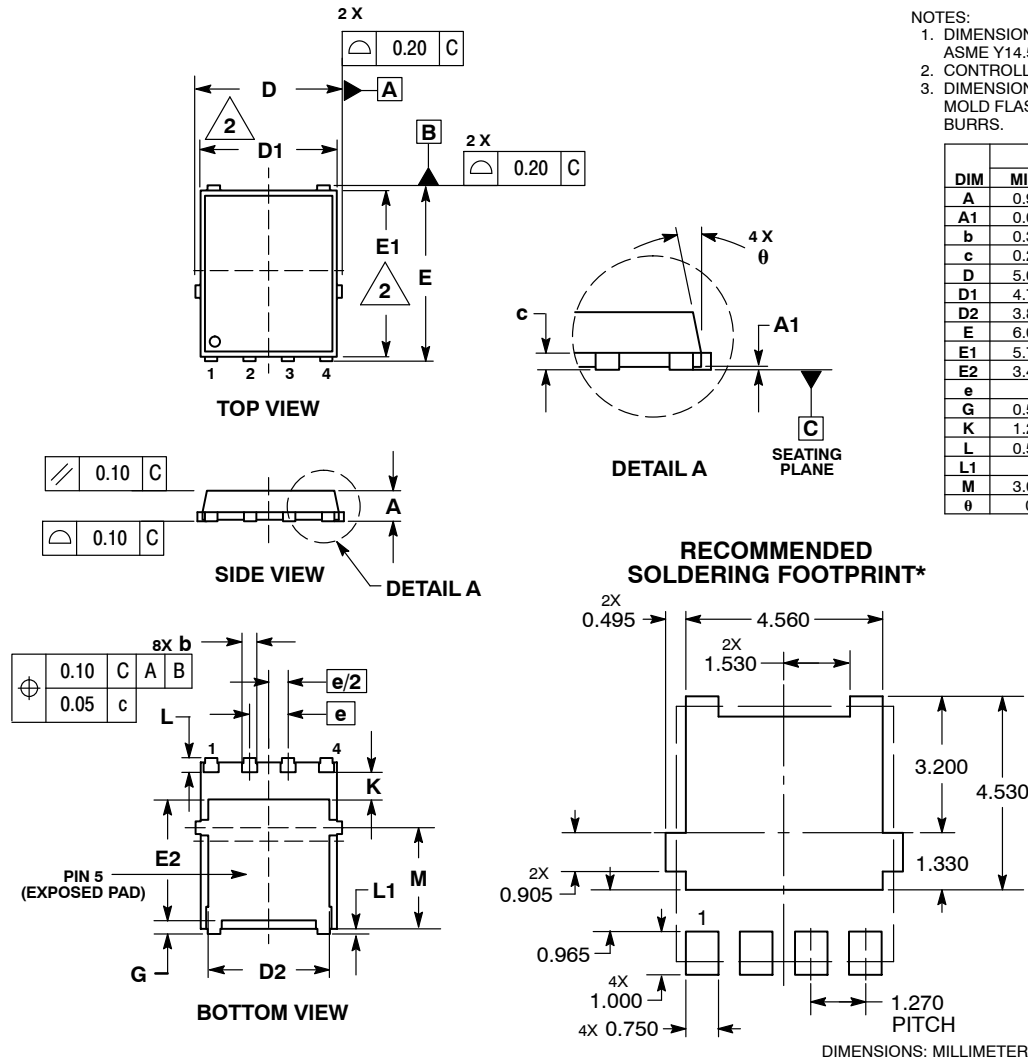


Figure 15. FET Thermal Response from Junction to Case

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PACKAGE DIMENSIONS

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE M



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	---	12 °

STYLE 1:

1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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